

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-250V	14Ω @ V <sub>GS</sub> = -10V	-0.26A
	18Ω @ V <sub>GS</sub> = -3.5V	-0.23A

## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

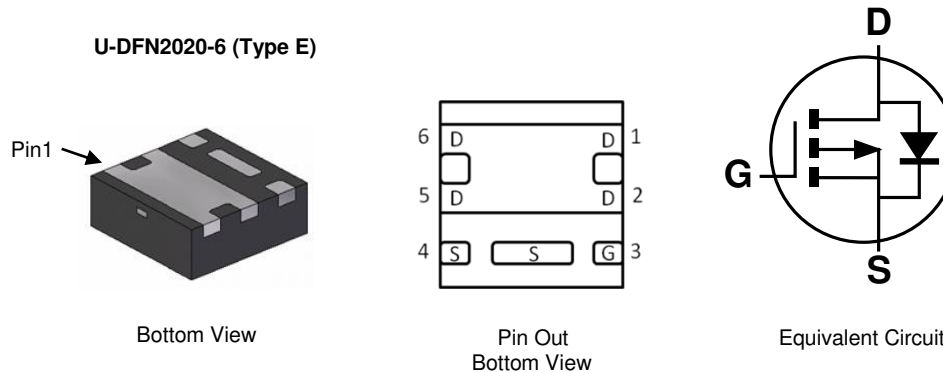
- General Purpose Interfacing Switch
- Load Switching
- Battery Management Application
- Power Management Functions

## Features and Benefits

- 0.6mm Profile – Ideal for Low-Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Weight: 0.0065 grams (Approximate)



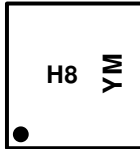
## Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Quantity per Reel
DMP25H18DLFDE-7	H8	7	3,000
DMP25H18DLFDE-13	H8	13	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

Site 1



H8 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

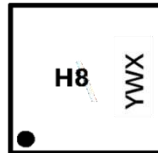
Date Code Key

<b>Year</b>	2014	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
<b>Code</b>	B	...	H	I	J	K	L	M	N	O	P	R

<b>Month</b>	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
<b>Code</b>	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



H8 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 0 = 2020)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

<b>Year</b>	2014	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
<b>Code</b>	4	...	0	1	2	3	4	5	6	7	8	9

<b>Week</b>	1-26	27-52	53
<b>Code</b>	A-Z	a-z	z

<b>Internal Code</b>	Sun	Mon	Tue	Wed	Thu	Fri	Sat
<b>Code</b>	T	U	V	W	X	Y	Z

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-250	V
Gate-Source Voltage			V <sub>GSS</sub>	±40	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-0.26 -0.21	A
Pulsed Drain Current (10µs Pulse, Duty Cycle ≤ 1%)			I <sub>DM</sub>	-1.0	A
Maximum Body Diode Continuous Current (Note 6)			I <sub>S</sub>	-0.26	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 5)	P <sub>D</sub>	0.6	W
	(Note 6)		1.4	
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>θJA</sub>	191	°C/W
	(Note 6)		86	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>θJC</sub>	17	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-250	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -250V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±40V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.5	-1.7	-2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	10	14	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -200mA V <sub>GS</sub> = -3.5V, I <sub>D</sub> = -100mA
			13	18		
Diode Forward Voltage	V <sub>SD</sub>	—	-0.8	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -200mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	81	—	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	14	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	4	—	pF	
Gate Resistance	R <sub>g</sub>	—	13	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	2.8	—	nC	V <sub>DS</sub> = -25V, I <sub>D</sub> = -200mA
Gate-Source Charge	Q <sub>gs</sub>	—	0.3	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.6	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	7.5	—	ns	V <sub>DS</sub> = -30V, I <sub>D</sub> = -200mA V <sub>GS</sub> = -10V, R <sub>G</sub> = 50Ω
Turn-On Rise Time	t <sub>R</sub>	—	25	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	124	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	95	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	85	—	ns	I <sub>F</sub> = -1.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	294	—	µC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

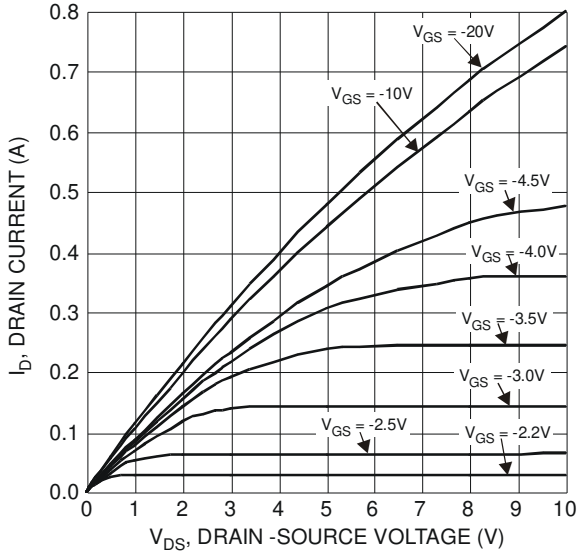


Figure 1 Typical Output Characteristics

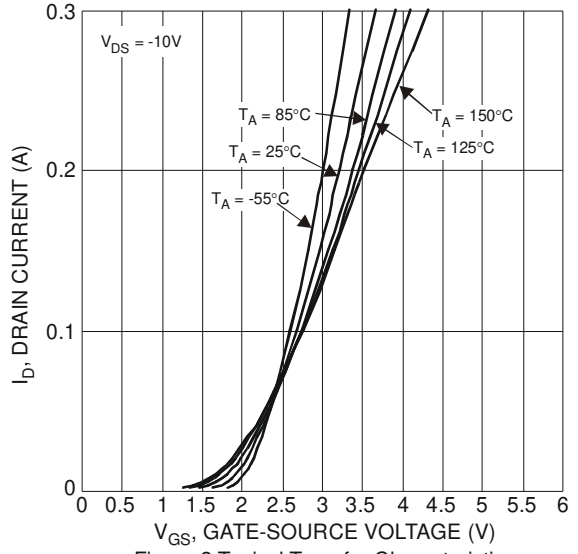


Figure 2 Typical Transfer Characteristics

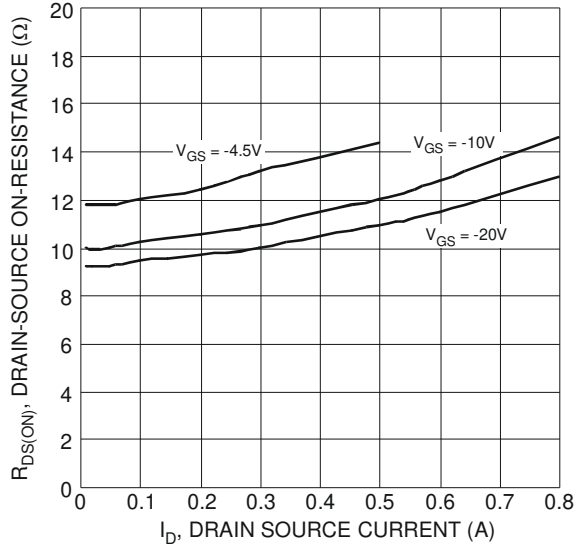


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

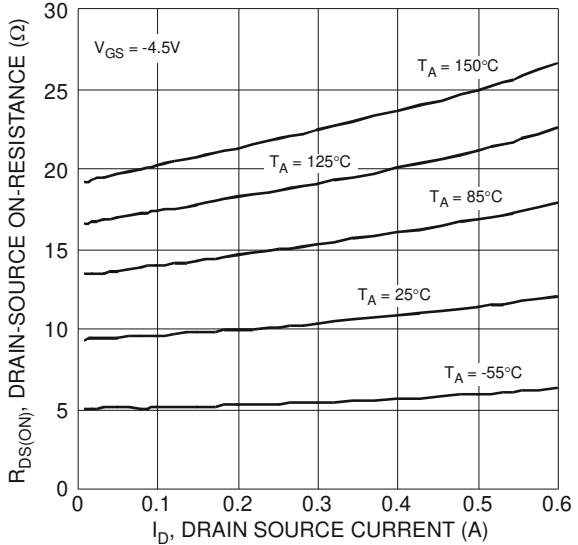


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

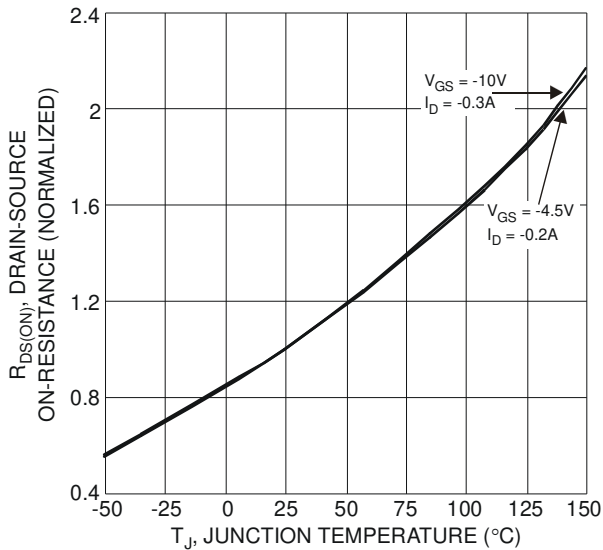


Figure 5 On-Resistance Variation with Temperature

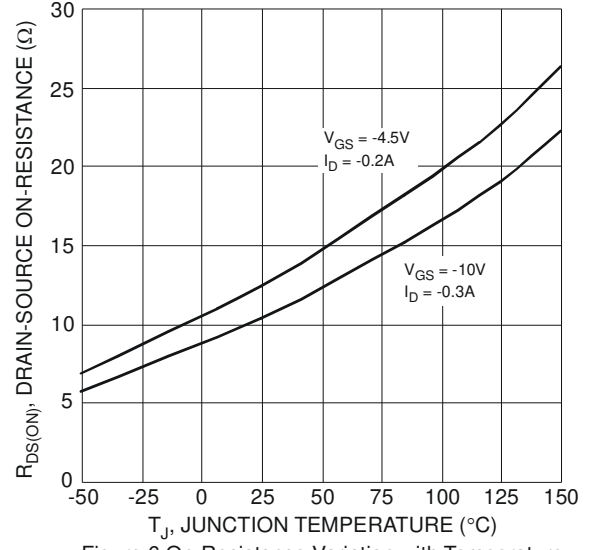


Figure 6 On-Resistance Variation with Temperature

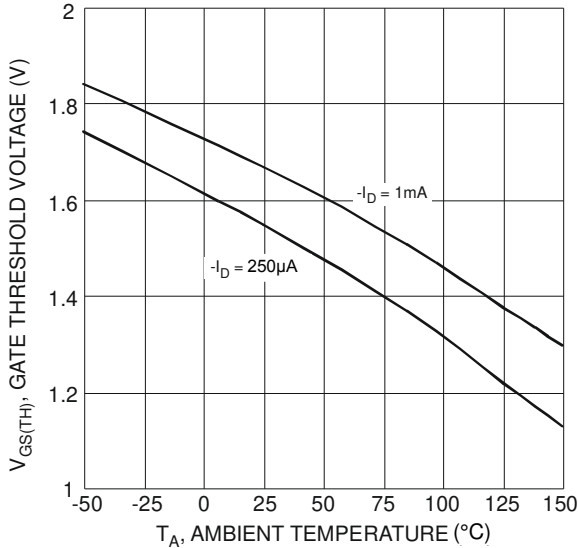


Figure 7 Gate Threshold Variation vs. Ambient Temperature

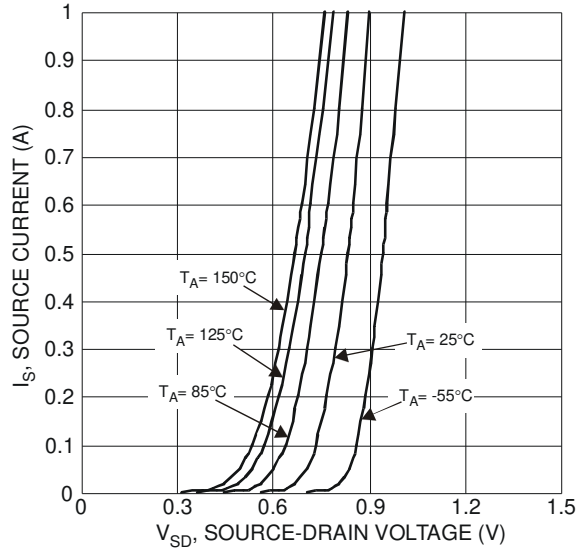


Figure 8 Diode Forward Voltage vs. Current

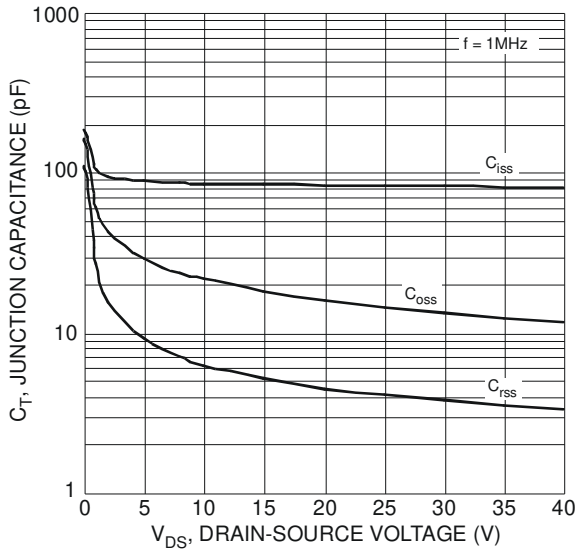


Figure 9 Typical Junction Capacitance

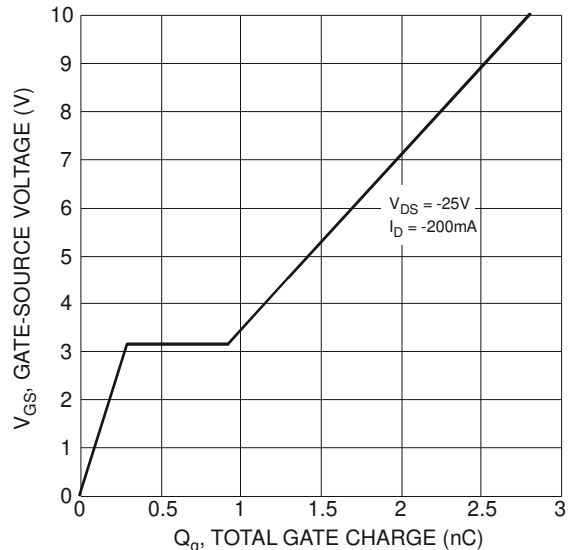


Figure 10 Gate-Charge Characteristics

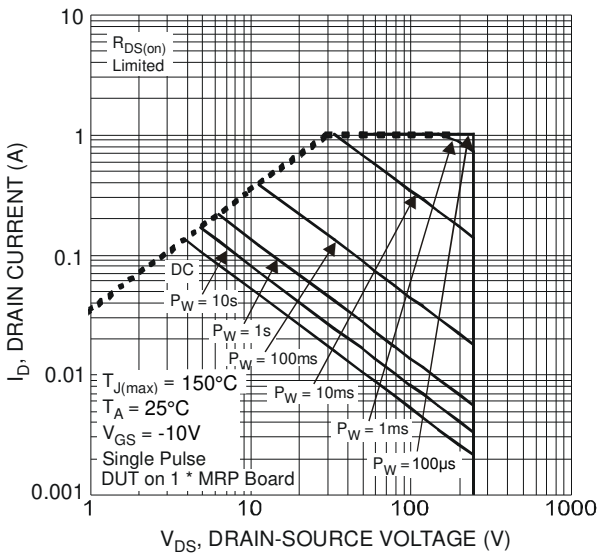


Figure 11 SOA, Safe Operation Area

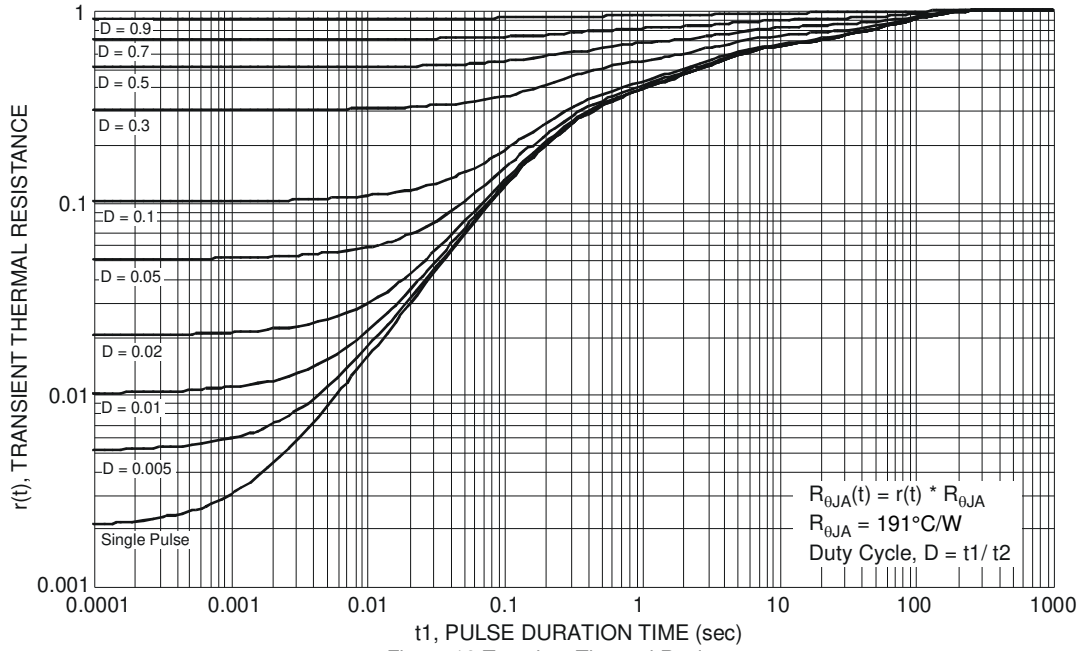
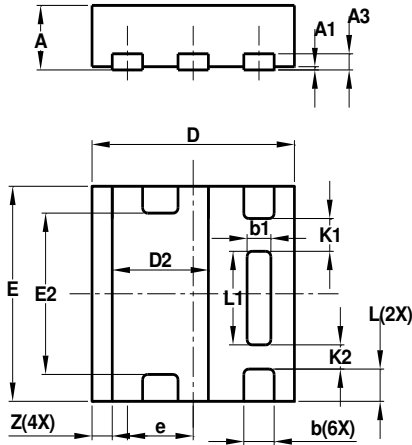


Figure 12 Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type E)**

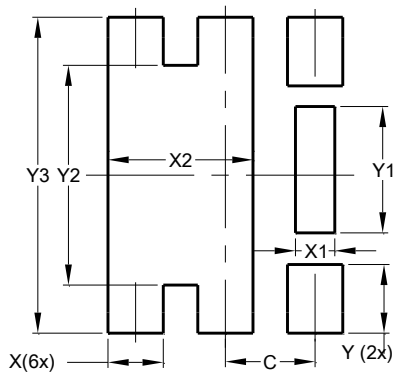


U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type E)**



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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